

Description

The AR3311D3 is a 3.3V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR3311D3 has a low capacitance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make AR3311D3 an ideal choice to protect cell phone, wireless systems, and communication equipment.

Features

- 340W peak pulse power (8/20 μs)
- Ultra low capacitance: 1pF typical
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 21A (8/20 μs)
- RoHS Compliant

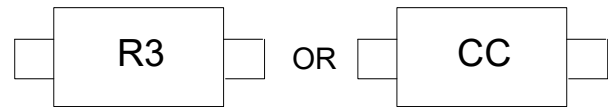
Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

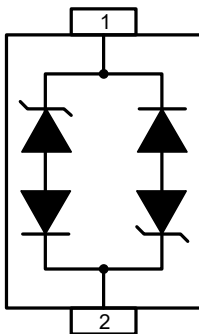
- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

Marking Information



R3 or CC = Device Marking Code

Equivalent Circuit and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AR3311D3	3000/Tape & Reel	7 inch

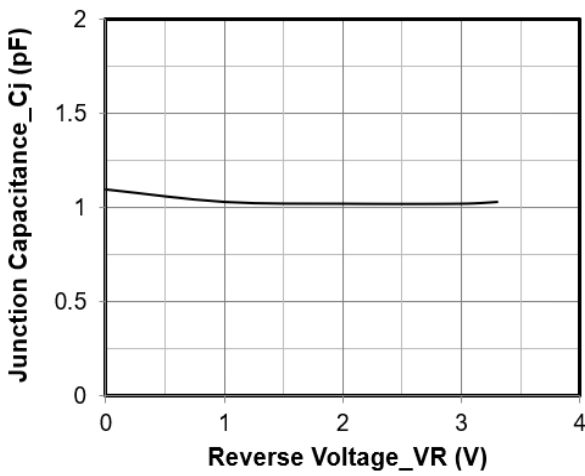
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P _{pk}	340	W
Peak Pulse Current (8/20μs)	I _{PP}	21	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±30	kV
ESD per IEC 61000-4-2 (Contact)		±30	
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

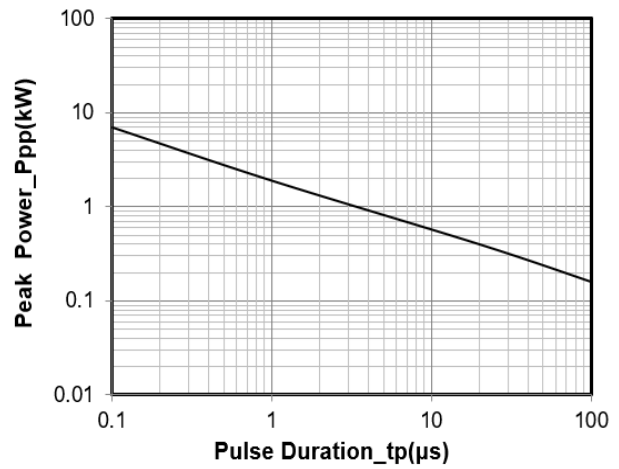
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Breakdown Voltage	V _{BR}	3.5			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 3.3V
Clamping Voltage	V _C			7	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V _C			16	V	I _{PP} = 21A (8 x 20μs pulse)
Junction Capacitance	C _J		1		pF	V _R = 0V, f = 1MHz

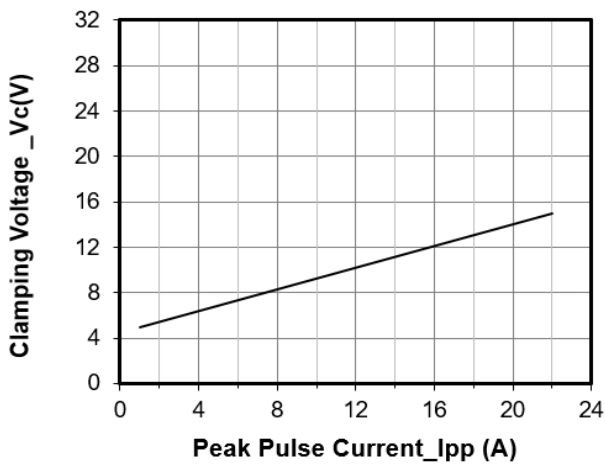
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



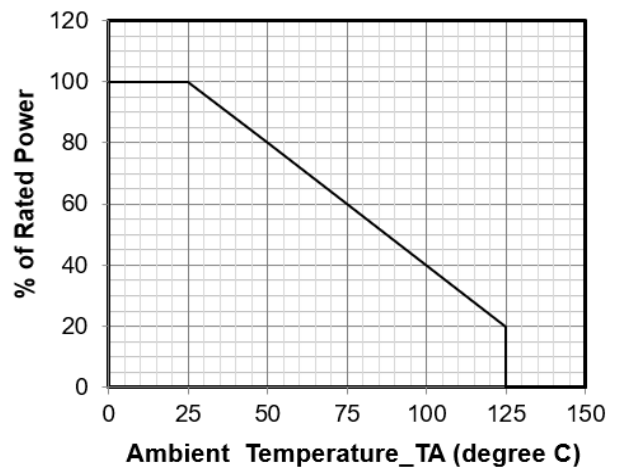
Junction Capacitance vs. Reverse Voltage



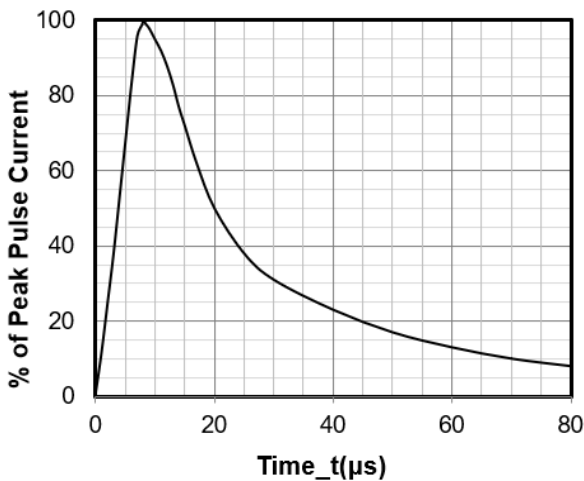
Peak Pulse Power vs. Pulse Time



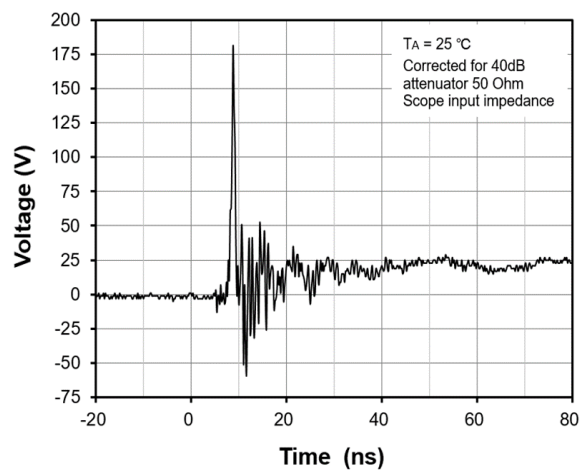
Clamping Voltage vs. Peak Pulse Current (tp = 8/20μs)



Power Derating Curve

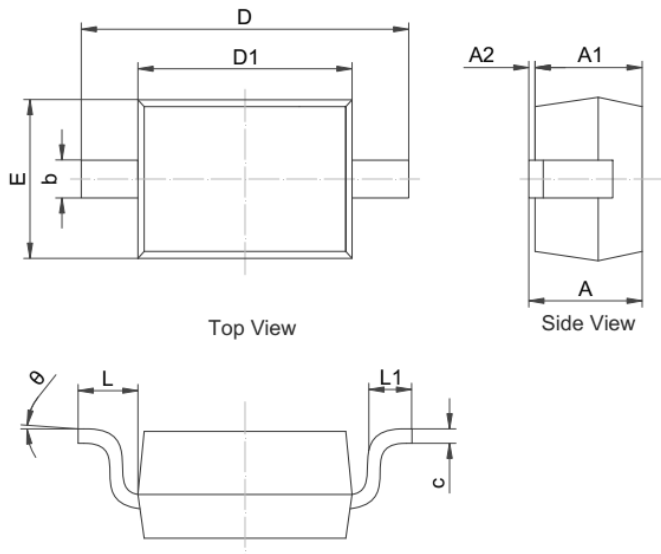


8 X 20μs Pulse Waveform



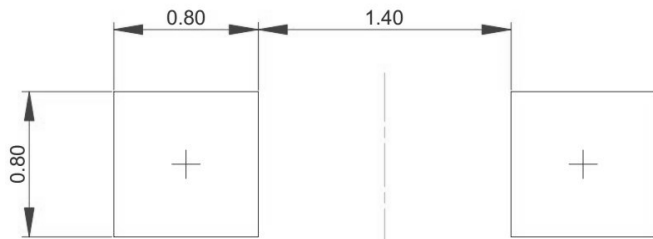
ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

SOD-323 Package Outline Drawing



	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	--	1.100
A1	0.800	--	0.900
A2	0.000	--	0.100
b	0.250	--	0.400
c	0.080	--	0.177
D1	1.600	1.700	1.800
D	2.300	--	2.800
E	1.150	--	1.400
L	0.475REF		
L1	0.100	--	0.500
Θ	0°	--	8°

Suggested Land Pattern



Unit: mm

Contact Information

Applied Power Microelectronics Inc.

Website: <http://www.appliedpowermicro.com>

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606